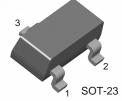


## **FJV3101R**

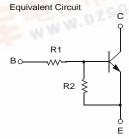
### Switching Application (Bias Resistor Built In)

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- WWW.DZSC.COM Built in bias Resistor (R1=4.7KΩ, R2=4.7KΩ)
- Complement to FJV4101R



1. Base 2. Emitter 3. Collector





## **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	50	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	10	V	
I <sub>C</sub>	Collector Current	100	mA	
P <sub>C</sub>	Collector Power Dissipation	200	mW	
TJ	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

## Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =10μA, I <sub>E</sub> =0	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>B</sub> =0	50		- 1777	V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =40V, I <sub>E</sub> =0		EC.	0.1	μА
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	20	WW		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA			0.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA		250		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0 f=1.0MHz		3.7		pF
V <sub>I</sub> (off)	Input Off Voltage	$V_{CE}=5V, I_{C}=100\mu A$	0.5			V
V <sub>I</sub> (on)	Input On Voltage	V <sub>CE</sub> =0.3V, I <sub>C</sub> =20mA			3	V
R <sub>1</sub>	Input Resistor		3.2	4.7	6.2	ΚΩ
R <sub>1</sub> /R <sub>2</sub>	Resistor Ratio		0.9	1	1.1	

## **Typical Characteristics**

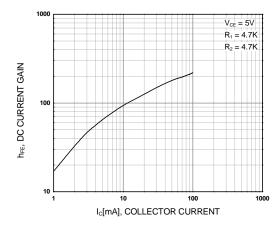


Figure 1. DC current Gain

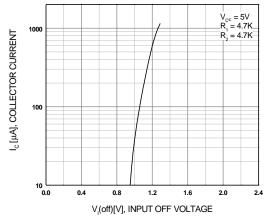


Figure 3. Input Off Voltage

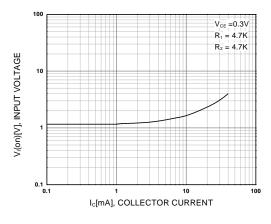


Figure 2. Input On Voltage

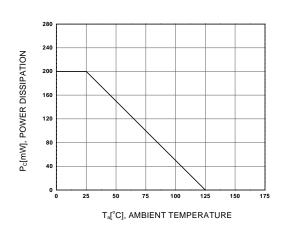
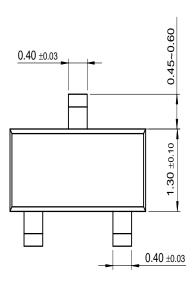


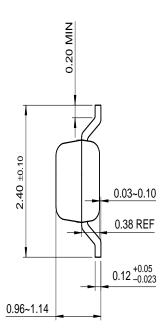
Figure 4. Power Derating

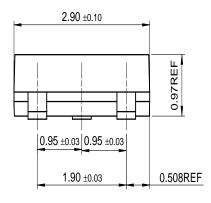
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# **Package Demensions**

# SOT-23







Dimensions in Millimeters

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EnSigna™	LittleFET™	QS™	TinyLogic™	
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